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## EXCHANGE COUPLING AND SPIN-FLIP TRANSITION OF $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$ BILAYERED FILMS

Tatsuo Fujii, Takuya Yano, Makoto Nakanishi and Jun Takada

Department of Applied Chemistry, Faculty of Engineering, Okayama University,  
Tsushima-naka 3-1-1, Okayama 700-8530, Japan

### ABSTRACT

$\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  (ferrimagnetic / antiferromagnetic) bilayered films were prepared on  $\alpha\text{-Al}_2\text{O}_3(102)$  single-crystalline substrates by helicon plasma sputtering. A well-crystallized epitaxial  $\alpha\text{-Fe}_2\text{O}_3(102)$  layer was formed on the substrate, while  $\text{CoFe}_2\text{O}_4$  grown on  $\alpha\text{-Fe}_2\text{O}_3(102)$  was a polycrystalline layer with a (100)-preferred orientation. The  $\alpha\text{-Fe}_2\text{O}_3(102)$  films without  $\text{CoFe}_2\text{O}_4$  layers clearly showed a spin-flip transition at about 400 K. The spins aligned perpendicular to the film plane at room temperature changed their direction within the film plane above 400 K. However the  $\alpha\text{-Fe}_2\text{O}_3$  base layers of  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered films did not show any spin-flip transition. The  $\text{CoFe}_2\text{O}_4$  layer on  $\alpha\text{-Fe}_2\text{O}_3$  had a large in-plane magnetic anisotropy, while the spin axis of the  $\alpha\text{-Fe}_2\text{O}_3(102)$  base layer was directed perpendicular to the film plane. The magnetization of ferrimagnetic  $\text{CoFe}_2\text{O}_4$  layers was coupled perpendicularly to the spin axis of antiferromagnetic  $\alpha\text{-Fe}_2\text{O}_3$  layers due to the exchange coupling at the interface between  $\text{CoFe}_2\text{O}_4$  and  $\alpha\text{-Fe}_2\text{O}_3$ .

### INTRODUCTION

Exchange coupling at an interface between ferromagnetic (FM) and antiferromagnetic (AFM) layers has received much attention mainly due to the technological applications in such devices as spin-valve sensors. It stabilizes a magnetic direction of the FM layer and functions as a bias field in the magnetic hysteresis loop. Recently, full micromagnetic calculations suggested the existence of the  $90^\circ$  FM - AFM coupling at the interface [1]. However the fundamental origin of exchange coupling between magnetic materials, especially magnetic oxide materials, is still unclear.  $\alpha\text{-Fe}_2\text{O}_3$  is one of candidates for the AFM materials fabricated in the spin-valve sensors [2,3]. The spin valves partly consisting of  $\alpha\text{-Fe}_2\text{O}_3$  have high thermal stability and large magneto-resistance ratio. By the way, one of the present authors found that epitaxial  $\alpha\text{-Fe}_2\text{O}_3(102)$  films on  $\alpha\text{-Al}_2\text{O}_3(102)$  had an unique spin-flip transition [4]. The transition takes place at about 400 K, much higher than the Morin transition temperature (260 K) of the bulk crystal. The spin axis lying within a film plane above 400 K turns perpendicular to the film plane below the transition temperature.

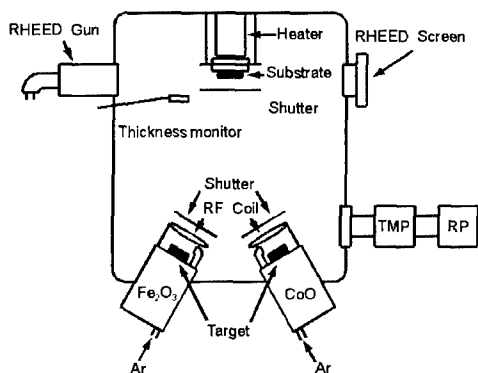
There are a few studies on the exchange coupling between oxide materials with the FM/AFM bilayered structure [5]. Most of practical FM oxides are exactly ferrimagnetic. Microscopic spin configurations at the interface between oxide systems could be different from the ones between metallic systems. We prepared well-crystallized  $\alpha\text{-Fe}_2\text{O}_3$  and  $\text{CoFe}_2\text{O}_4$  bilayered films by using helicon plasma sputtering technique [6].  $\text{CoFe}_2\text{O}_4$  is a typical ferrimagnetic material with an inverse spinel structure. Structural properties and magnetic interactions between ferrimagnetic  $\text{CoFe}_2\text{O}_4$  (FM) and  $\alpha\text{-Fe}_2\text{O}_3$  (AFM) layers were discussed. If the exchange coupling at the  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  interface was strong enough, magnetic properties of the  $\text{CoFe}_2\text{O}_4$  layer should be influenced by the spin-flip transition of the  $\alpha\text{-Fe}_2\text{O}_3$  layer or vice versa.

## EXPERIMENT

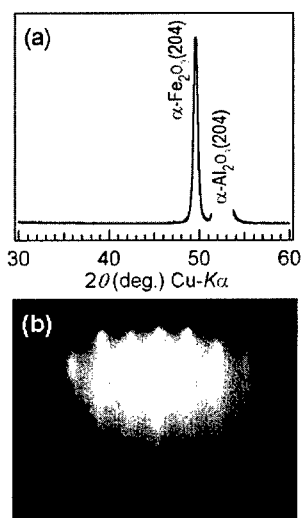
Helicon plasma sputtering is a powerful technique to prepare high-quality multilayered films with sharp interfaces [7]. It has some advantages in comparison with conventional rf magnetron sputtering, such as high deposition rate stability and low plasma damage to the film surface. A helicon plasma cathode consists of a conventional rf magnetron cathode and a rf coil for a helicon wave. Fig.1 shows a schematic drawing of the helicon plasma sputtering system we used. Two targets for helicon cathodes were made of sintered  $\alpha\text{-Fe}_2\text{O}_3$  and CoO, respectively. The base pressure of the system was  $10^{-7}$  Pa. Before sputter deposition an  $\alpha\text{-Al}_2\text{O}_3(102)$  substrate was annealed in vacuum at about 973 K for 1 hour in order to obtain a clean and well-ordered surface.  $\alpha\text{-Fe}_2\text{O}_3$  base layers with the thickness of 100 nm were sputtered on the substrate at the substrate temperature of 673 K.  $\text{CoFe}_2\text{O}_4$  layers with several thicknesses ranging from 25 to 200 nm were then deposited on  $\alpha\text{-Fe}_2\text{O}_3$  at 773 K by simultaneous sputtering from both targets, to control the deposition rate ratio between  $\alpha\text{-Fe}_2\text{O}_3$  and CoO. The deposited films were characterized by reflection high energy electron diffraction (RHEED), x-ray diffraction (XRD), scanning probe microscopy (SPM), vibrating sample magnetometer (VSM), conversion electron Mössbauer spectroscopy (CEMS), and energy dispersive X-ray spectroscopy (EDS).

## RESULTS AND DISCUSSION

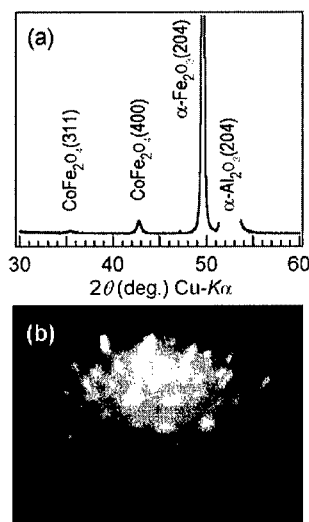
Typical XRD and RHEED patterns of  $\alpha\text{-Fe}_2\text{O}_3$  films deposited on  $\alpha\text{-Al}_2\text{O}_3(102)$  single-crystalline substrates are shown in figs. 2(a) and (b), respectively. Epitaxial relationship between the  $\alpha\text{-Fe}_2\text{O}_3$  layer and the  $\alpha\text{-Al}_2\text{O}_3$  substrate can clearly be seen in both XRD and RHEED patterns. The XRD pattern had only a reflection from the film indexed as  $\alpha\text{-Fe}_2\text{O}_3(204)$  at the side of an intense  $\alpha\text{-Al}_2\text{O}_3(204)$  reflection. The sharp streak lines in the RHEED pattern indicated an atomically flat surface of the layer. Both  $\alpha\text{-Fe}_2\text{O}_3$  and  $\alpha\text{-Al}_2\text{O}_3$  have a corundum structure with a small lattice misfit of +5.8 %. This could be a reason why the well-crystallized and atomically flat  $\alpha\text{-Fe}_2\text{O}_3$  layers were epitaxially formed on the  $\alpha\text{-Al}_2\text{O}_3$  substrates.



**Figure 1.** Schematic drawing of helicon plasma sputtering system we used. The helicon cathodes consist of conventional rf magnetron cathodes and rf coils.



**Figure 2.** (a) XRD and (b) RHEED patterns of an  $\alpha\text{-Fe}_2\text{O}_3$  film deposited on an  $\alpha\text{-Al}_2\text{O}_3$  (102) substrate.

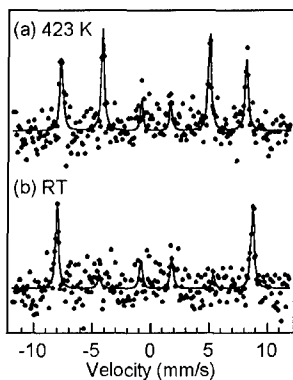


**Figure 3.** (a) XRD and (b) RHEED patterns of a  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered film deposited on an  $\alpha\text{-Al}_2\text{O}_3$  (102) substrate. Thicknesses of the  $\text{CoFe}_2\text{O}_4$  and the  $\alpha\text{-Fe}_2\text{O}_3$  layers were 200 and 100 nm, respectively.

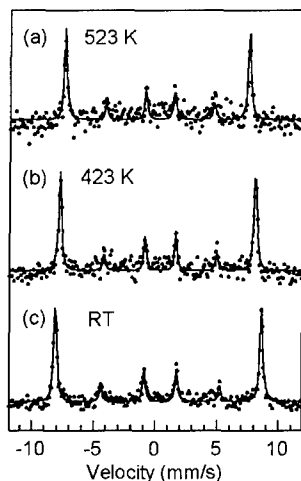
Figs. 3(a) and (b) are typical XRD and RHEED patterns of  $\text{CoFe}_2\text{O}_4/\text{Fe}_2\text{O}_3$  bilayered films, respectively. The XRD pattern of the  $\text{CoFe}_2\text{O}_4/\text{Fe}_2\text{O}_3$  bilayered film had two reflections from the  $\text{CoFe}_2\text{O}_4$  layer indexed as  $\text{CoFe}_2\text{O}_4$ (311) and (400) in addition to the reflection from the  $\alpha\text{-Fe}_2\text{O}_3$  (204) base layer. The relative peak intensity ratio of  $\text{CoFe}_2\text{O}_4$ (400) to (311) was considerably large, in comparison with that of the  $\text{CoFe}_2\text{O}_4$  bulk pattern with random orientation [8]. The  $\text{CoFe}_2\text{O}_4$  layer formed on  $\alpha\text{-Fe}_2\text{O}_3$ (102) had strong (100)-preferred orientation. In crystallographic aspects, the  $\alpha\text{-Fe}_2\text{O}_3$ (102) surface has a pseudo-square structure though the  $\alpha\text{-Fe}_2\text{O}_3$  crystal has hexagonal corundum structure. The  $\text{CoFe}_2\text{O}_4$ (100) layer with cubic spinel structure could be formed on the  $\alpha\text{-Fe}_2\text{O}_3$ (102) base layer. However the lattice misfit between them is very large, about  $\sim 17\%$ . The RHEED pattern of  $\text{CoFe}_2\text{O}_4$  on  $\alpha\text{-Fe}_2\text{O}_3$ (102) was spotted and complicated. The  $\text{CoFe}_2\text{O}_4$  layers in bilayered films were poly-crystallized and had (100)-preferred orientation. Moreover, chemical formula of the  $\text{CoFe}_2\text{O}_4$  layer analyzed by EDS was  $\text{Co}_{0.7}\text{Fe}_{2.3}\text{O}_4$ .

The spin direction of  $\alpha\text{-Fe}_2\text{O}_3$  layers on  $\alpha\text{-Al}_2\text{O}_3$ (102) was easily determined by CEMS. The CEMS spectrum of  $\alpha\text{-Fe}_2\text{O}_3$  generally exhibited six lines due to the nuclear Zeeman splitting from a large internal magnetic field. Relative peak intensity ratio of the sextet is expressed theoretically as a function of an angle ( $\theta$ ) between the  $\gamma$ -ray direction and the spin direction

$$3 : \frac{4 \sin^2 \theta}{1 + \cos^2 \theta} : 1 : 1 : \frac{4 \sin^2 \theta}{1 + \cos^2 \theta} : 3.$$



**Figure 4.** CEMS spectra of an  $\alpha\text{-Fe}_2\text{O}_3(102)$  film deposited on  $\alpha\text{-Al}_2\text{O}_3(102)$  measured at (a) 423 K and (b) room temperature.



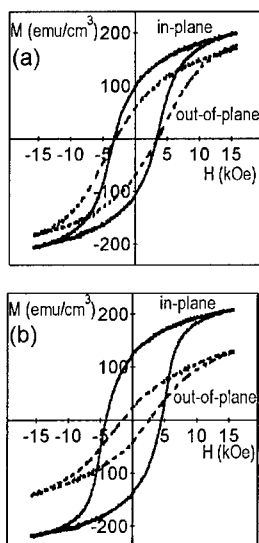
**Figure 5.** CEMS spectra of a  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered film on  $\alpha\text{-Al}_2\text{O}_3(102)$ , measured at (a) 523 K, (b) 423 K, and (c) room temperature. Thicknesses of the  $\text{CoFe}_2\text{O}_4$  and  $\alpha\text{-Fe}_2\text{O}_3$  layers were 25 and 100 nm, respectively.

CEMS spectra of an  $\alpha\text{-Fe}_2\text{O}_3(102)$  film without a  $\text{CoFe}_2\text{O}_4$  covering layer are shown in fig. 4 as a function of the temperature. The spectra had the intensity ratio of nearly 3:0:1:1:0:3 at 300 K and 3:4:1:1:4:3 at 423 K. The spin axis of the  $\alpha\text{-Fe}_2\text{O}_3(102)$  film was abruptly changed from the perpendicular direction ( $\theta=0^\circ$ ) to the in-plane direction ( $\theta=90^\circ$ ) at about 400 K.

Besides the intensity ratio of the CEMS spectra of the  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3(102)$  bilayered film did not show any temperature dependence, even when the  $\alpha\text{-Fe}_2\text{O}_3(102)$  layer was covered by a very thin, 25 nm-thick,  $\text{CoFe}_2\text{O}_4$  layer. All spectra of the  $\alpha\text{-Fe}_2\text{O}_3(102)$  base layer had the intensity ratio of about 3:0:1:1:0:3 as shown in fig. 5. The  $\alpha\text{-Fe}_2\text{O}_3$  layer covered by  $\text{CoFe}_2\text{O}_4$  did not show the spin-flip transition. The spin direction in  $\alpha\text{-Fe}_2\text{O}_3$  was fixed perpendicular to the film plane over the all temperatures.

In-plane and out-of-plane magnetization curves of the  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered films were also measured at various temperatures. Figs. 6(a) and (b) show room temperature magnetization curves of the 200 nm-thick  $\text{CoFe}_2\text{O}_4$  films without and with the  $\alpha\text{-Fe}_2\text{O}_3(102)$  base layers, respectively. No uniaxial magnetic anisotropy nor exchange bias field was induced in the  $\text{CoFe}_2\text{O}_4$  layers, when they did not have the  $\alpha\text{-Fe}_2\text{O}_3$  base layers.  $\text{CoFe}_2\text{O}_4$  is known to have a large magnetocrystalline anisotropy along the  $\langle 100 \rangle$  direction [8]. The (100)-oriented  $\text{CoFe}_2\text{O}_4$  layers could have domain structures magnetized along the in-plane [100] and [010] and the out-of-plane [001] directions. The large coercivity was, thus, observed in both in-plane and out-of-plane hysteresis loops.

On the other hands, the  $\text{CoFe}_2\text{O}_4$  layers deposited on the  $\alpha\text{-Fe}_2\text{O}_3(102)$  base layers had a large in-plane magnetic anisotropy. The exchange bias field of about 200 Oe was induced. The spin



**Figure 6.** In-plane and out-of-plane magnetization curves of (a) a 200 nm-thick  $\text{CoFe}_2\text{O}_4$  film deposited on  $\alpha\text{-Al}_2\text{O}_3(102)$ , and (b) a  $\text{CoFe}_2\text{O}_4(200 \text{ nm})/\alpha\text{-Fe}_2\text{O}_3(100 \text{ nm})$  bilayered film on  $\alpha\text{-Al}_2\text{O}_3(102)$ . The magnetization curves were measured at room temperature

axis of the  $\alpha\text{-Fe}_2\text{O}_3$  base layers was directed perpendicular to the film plane as discussed above. The magnetization of the  $\text{CoFe}_2\text{O}_4$  (FM) layers was exactly coupled perpendicularly to the spin axis of the  $\alpha\text{-Fe}_2\text{O}_3$  (AFM) layers. The  $90^\circ$  FM-AFM coupling observed in  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered films was in good agreement with the theoretical result reported by Koon [1]. The large in-plane anisotropy of the  $\text{CoFe}_2\text{O}_4$  layers was probably induced by the  $90^\circ$  coupling with the  $\alpha\text{-Fe}_2\text{O}_3$  layers and it should suppress the spin-flip transition of the  $\alpha\text{-Fe}_2\text{O}_3$  layers irreversibly.

## SUMMARY

Exchange coupling between a ferrimagnetic  $\text{CoFe}_2\text{O}_4$  layer and an antiferromagnetic  $\alpha\text{-Fe}_2\text{O}_3$  layer was examined to prepare  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered films. (100)-oriented  $\text{CoFe}_2\text{O}_4$  layers were formed on well-crystallized epitaxial  $\alpha\text{-Fe}_2\text{O}_3(102)$  layers deposited on  $\alpha\text{-Al}_2\text{O}_3(102)$  single-crystalline substrates. The  $\alpha\text{-Fe}_2\text{O}_3(102)$  films without  $\text{CoFe}_2\text{O}_4$  layers clearly showed the spin-flip transition at about 400 K. The spin axis lay within the (102) plane of  $\alpha\text{-Fe}_2\text{O}_3$  at high temperatures but became almost normal to the plane at low temperatures. However the  $\alpha\text{-Fe}_2\text{O}_3(102)$  layers covered by  $\text{CoFe}_2\text{O}_4$  layers did not show any spin-flip transition. The spin axis of the  $\alpha\text{-Fe}_2\text{O}_3(102)$  base layers was fixed on the perpendicular to the films. Magnetic hysteresis loops of  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  bilayered films indicated that a large in-plane magnetic anisotropy and an exchange bias field were induced in the films. The  $90^\circ$  coupling at the interface between ferrimagnetic and antiferromagnetic materials was directly observed in the  $\text{CoFe}_2\text{O}_4/\alpha\text{-Fe}_2\text{O}_3$  system fabricated entirely of oxides.

## ACKNOWLEDGEMENT

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